



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1762

#3/A
2-21-03

Applicant: Ning Docket No.: 01-P-18264 US
Serial No.: 10/057,575 Art Unit: 1762
Filed: 1/25/2002 Examiner: TBD
For: Vertical MIMCap Manufacturing Method

Certificate of Mailing via First Class Mail

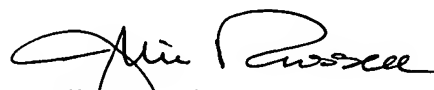
RECEIVED
JAN 28 2003
TC 1700

Date of Deposit: January 22, 2003

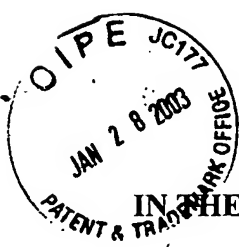
I hereby certify that the below listed correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231.

Certificate of Mailing via First Class Mail (1 page)
Preliminary Amendment (11 pages)
Return Postcard

Respectfully submitted,


Julie Russell
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#3/A

2-31-03

Applicant: Ning

Docket No.: 01-P-18264 US

Serial No.: 10/057,575

Art Unit: 1762

Filed: 1/25/2002

Examiner: TBD

Title: Vertical MIMCap Manufacturing Method

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

RECEIVED
JAN 29 2003
TC 1700

Dear Sirs:

Prior to examination on the merits of the above patent application, the Applicant respectfully submits this Preliminary Amendment and remarks as set forth below:

In the Specification:

Please amend paragraph beginning on ~~page 3, line 33~~, as follows:

AI
In one embodiment, disclosed is a method of fabricating a vertical MIMCap, comprising providing a wafer having a workpiece, depositing an insulating layer over the workpiece, and patterning the insulating layer with a plurality of trenches. The insulating layer comprises at least one first region and at least one second region, and the first region comprises trenches for at least one MIMCap. The method includes depositing a first conductive layer over the insulating layer within the trenches, depositing a resist over the insulating layer first regions, and depositing a second conductive material within the insulating layer second region trenches. The resist is removed, and a thin dielectric layer is deposited over the insulating layer first region within the first region trenches. A third conductive material is deposited over the thin dielectric layer within the first region trenches.